1N5829, 1N5830
1N5831
MBR5831,H, H1

MOTOROLA

Designers Data Sheet

HOT CARRIER POWER RECTIFIERS

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

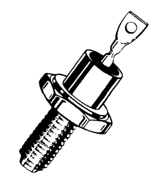
- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- High Surge Capacity
- TX Version Available

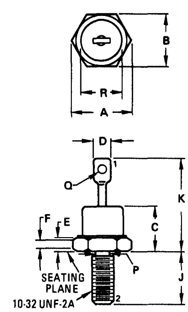
Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

SCHOTTKY BARRIER RECTIFIERS

25 AMPERE
20, 30, 40 VOLTS





STYLE 2:
TERM 1. ANODE
2. CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	11.94	12.83	0.470	0.505
B	10.77	11.10	0.424	0.437
C	–	10.29	–	0.405
D	–	6.35	–	0.250
E	1.91	4.45	0.075	0.175
F	1.52	–	0.060	–
J	10.72	11.51	0.422	0.453
K	–	20.32	–	0.800
P	4.14	4.80	0.163	0.189
Q	1.52	–	0.060	–
R	–	10.77	–	0.424

All JEDEC dimensions and notes apply

CASE 56
D0-4

*MAXIMUM RATINGS

Rating	Symbol	1N 5829	1N 5830	1N 5831 MBR 5831H,H1	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	24	36	48	Volts
Average Rectified Forward Current $V_{R(equiv)} \leq 0.2\ V_{R\ (dc)}$, $T_C = 85°C$	I_O	← 25 →			Amp
Ambient Temperature Rated $V_{R\ (dc)}$, $P_{F(AV)} = 0$ $R_{\theta JA} = 3.5°C/W$	T_A	90	85	80	°C
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase 60 Hz)	I_{FSM}	800 (for 1 cycle)			Amp
Operating and Storage Junction Temperature Range (Reverse voltage applied	T_J, T_{stg}	← -65 to +125 →			°C
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	← 150 →			°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.75	°C/W

*ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	1N 5829	1N 5830	1N 5831 MBR 5831H, H1	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 10 Amp) (i_F = 25 Amp) (i_F = 78.5 Amp)	v_F	 0.360 0.440 0.720	 0.370 0.460 0.770	 0.380 0.480 0.820	Volts
Maximum Instantaneous Reverse Current @ Rated dc Voltage (1) (T_C = 100°C)	i_R	 20 150	 20 150	 20 150	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0% *Indicates JEDEC Registered Data for 1N5829–1N5831

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and terminal leads are readily solderable.
POLARITY: Cathode to Case
MOUNTING POSITIONS: Any
STUD TORQUE: 15 in. lb. Max

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NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.2 V_{RWM}. Proper derating may be accomplished by use of equation (1):

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}\,P_{F(AV)} - R_{\theta JA}\,P_{R(AV)} \quad (1)$$

where

$T_{A(max)}$ = Maximum allowable ambient temperature

$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest).

$P_{F(AV)}$ = Average forward power dissipation

$P_{R(AV)}$ = Average reverse power dissipation

$R_{\theta JC}$ = Junction-to-ambient thermal resistance

Figures 1, 2 and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2):

$$T_R = T_{J(max)} - R_{\theta JA}\,P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA}\,P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2 and 3 as a difference in the rate of change of the slope in the vicinity of 115°C. The data of Figures 1, 2 and 3 is based upon dc conditions. For use in common rectifier circuits, Table I indicates suggested factors for an equivalent dc voltage to use for conservative design; i.e.:

$$V_{R(equiv)} = V_{in(PK)} \times F \quad (4)$$

The Factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

Example: Find $T_{A(max)}$ for 1N5831 operated in a 12-Volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 16 A ($I_{F(AV)}$ = 8 A), $I_{(PK)}/I_{(AV)}$ = 20, Input Voltage = 10 V(rms), $R_{\theta JA}$ = 5°C/W.

Step 1: Find $V_{R(equiv)}$. Read F = 0.65 from Table I ∴ $V_{R(equiv)}$ = (1.41)(10)(0.65) = 9.18 V

Step 2: Find T_R from Figure 3. Read T_R = 113°C @ V_R = 9.18 & $R_{\theta JA}$ = 5°C/W

Step 3: Find $P_{F(AV)}$ from Figure 4.** Read $P_{F(AV)}$ = 12.8 W @ $\frac{I_{(PK)}}{I_{(AV)}}$ = 20 & $I_{F(AV)}$ = 8 A

Step 4: Find $T_{A(max)}$ from equation (3). $T_{A(max)}$ = 113-(5)(12.8) = 49°C

** Value given are for the 1N5828. Power is slightly lower for the other units because of their lower forward voltage.

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TABLE I — VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave, Center Tapped *†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

*Note that $V_{R(PK)} \approx 2\,V_{in(PK)}$

*†Use line to center tap voltage for V_{in}.

FIGURE 1 — MAXIMUM REFERENCE TEMPERATURE — 1N5829

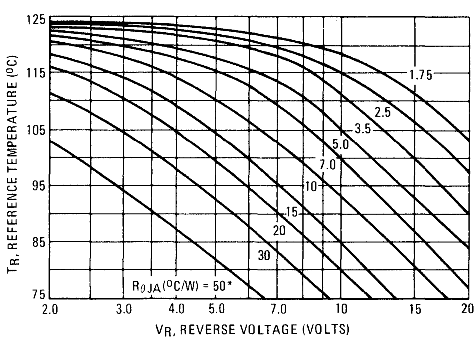


FIGURE 2 — MAXIMUM REFERENCE TEMPERATURE — 1N5830

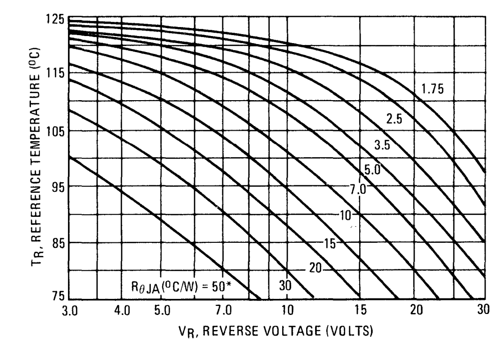
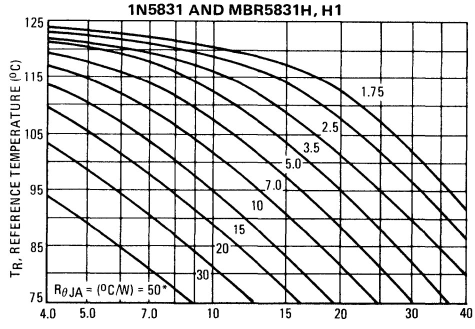


FIGURE 3 — MAXIMUM REFERENCE TEMPERATURE 1N5831 AND MBR5831H, H1



*No external heat sink.

FIGURE 4 — FORWARD POWER DISSIPATION

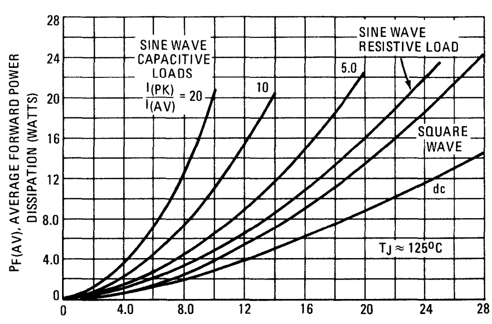


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FIGURE 5 — TYPICAL FORWARD VOLTAGE

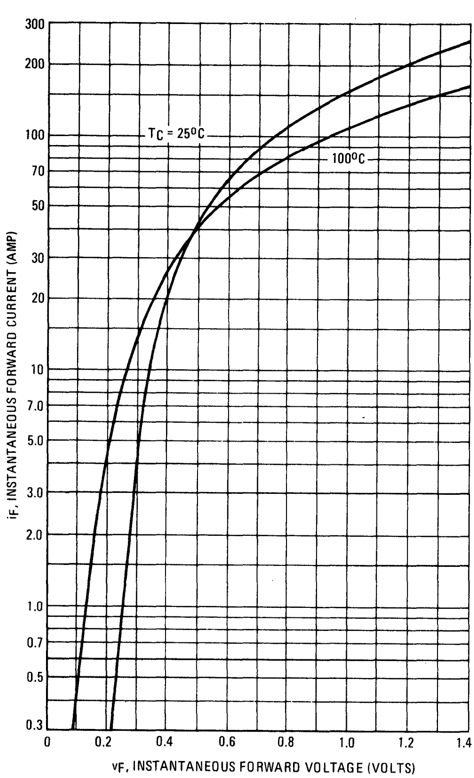


FIGURE 6 — MAXIMUM SURGE CAPABILITY

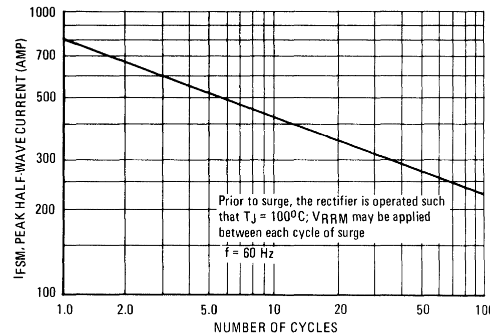


FIGURE 7 — CURRENT DERATING

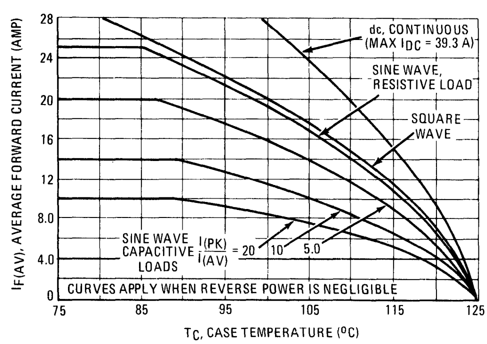


FIGURE 8 — THERMAL RESPONSE

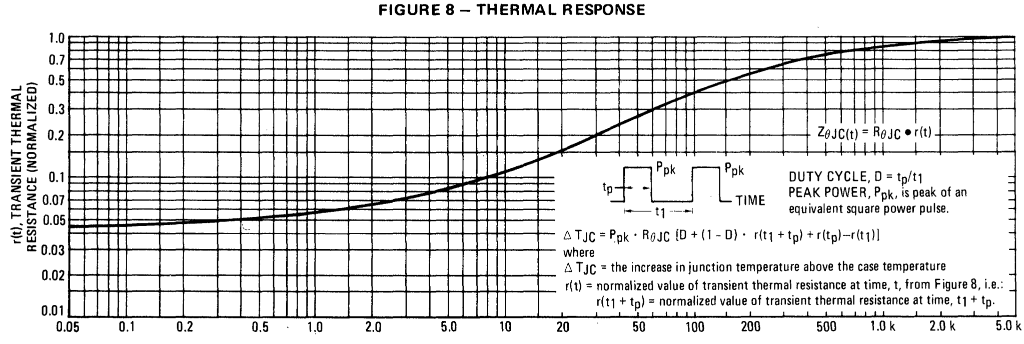


FIGURE 9 – NORMALIZED REVERSE CURRENT

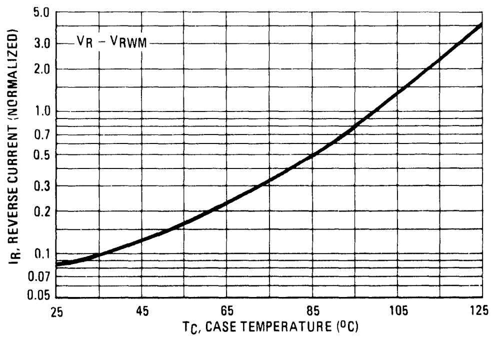


FIGURE 10 – TYPICAL REVERSE CURRENT

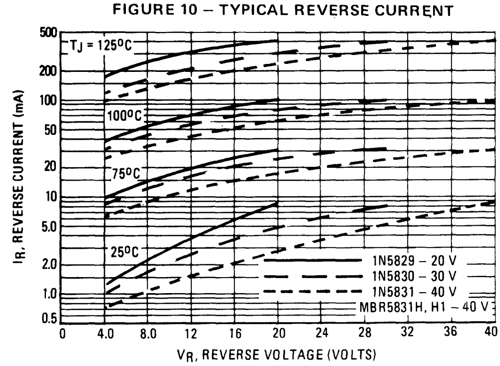
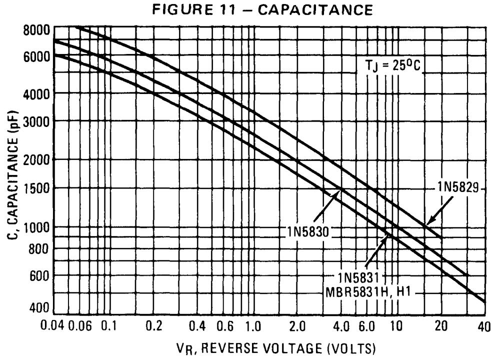


FIGURE 11 – CAPACITANCE

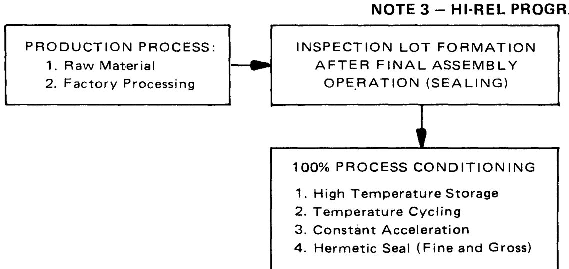


NOTE 2 – HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 11).

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

NOTE 3 – HI-REL PROGRAM OPTIONS



The 1N5831 is also available with two levels of extra testing similar to "TX" screening and including Group A and B inspection programs. Both the MBR5831H and MBR5831H1 go through 100% screening consisting of high temperature storage, temperature cycling, constant acceleration and hermetic seal testing prior to a sample being submitted to Group A and B inspection. After completion of Group B inspection, the MBR5831H is available without additional screening. MBR5831H1 devices are further processed through a high temperature reverse bias (HTRB) and forward burn-in. Consult factory for details.